

# L9341

# QUAD LOW SIDE DRIVER

#### AVANCE DATA

- DU/DT AND DI/DT CONTROL
- PWM CONTROLLED OUTPUT CURRENT
- SHORT CURRENT PROTECTION AND DI-AGNOSTIC
- INTEGRATED FLYBACK DIODE
- UNDERVOLTAGE SHUTDOWN
- OVERVOLTAGE AND UNDERVOLTAGE DI-AGNOSTIC
- OVERTEMPERATURE DIAGNOSTIC

#### DESCRIPTION

The L9341 is a monolithic integrated circuit realized in Multipower BCD-II mixed technology. The driver is intended for inductive loads in synchronous PWM applications, especially for valve driv-



#### **BLOCK & APPLICATION DIAGRAM**

ers. The output voltage and current rise and fall slopes du/dt and di/dt are controlled.



This is advanced information on a new product now in development or undergoing evaluation. Details are subject to change without notice.

### **PIN CONNECTION** (Top view)



#### **ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	V <sub>CC</sub> Voltage Range	-0.3 to 6	V
Vs	V <sub>S</sub> Voltage Range	-0.3 to 24	V
V <sub>spmax</sub>	VS Voltage Range for t ≤ 400ms	-2 to 40	V
V <sub>st</sub>	Schaffner Transient Pulses on VS	see note 1	V
Vin	Input Voltage Range for SDI; SCLK;CS;RES1;RES2	-0.3to V <sub>CC</sub> +0.3	
V <sub>out</sub>	Output Voltage Range for all Outputs: Negative Positive	$-$ 0.3 intern. clamped to $V_{\rm S}$	V V
l <sub>out</sub>	Output Current for all Outputs: Negative Positive	-2 +2	A A
	for Transient with t < 10ms Negative Positive	- 5 5	A A
	Schaffner Transient Pulses on Output	see note 2	
VESD	ESD Voltage Capability (MIL 883 C)	1500	V

#### THERMAL DATA

Symbol	Parameter	Value	Unit
R <sub>th j-case</sub>	Thermal Resistance Junction to Case	3	°C/W
R <sub>th j-amb</sub>	Thermal Resistance Junction to Ambient mounted on PC Board	35	°C/W
T <sub>sdh</sub>	Thermal Hysteresis	20	°C
T <sub>sd</sub>	Thermal Diagnostic	T <sub>j</sub> > 150	°C

#### Notes:

Schaffner transient specification: DIN 40839 test waveforms of the following type: 1, 2, 3a, 3b, 5 and 6. The pulses are applied to the application circuit according to fig. 3.

2. The maximum output current results from the Schaffner pulses specified in note 1.



**ELECTRICAL CHARACTERISTICS** (Unless otherwise specified:  $8V \le V_S \le 24V$ ;  $4.7V \le V_{CC} \le 5.3V$ ;  $-40 \ ^\circ\text{C} \le Tj \le 150 \ ^\circ\text{C}$ ;  $I_O \le 1A$  (note 3);  $I_O \le 1.5A$ ;  $V_{sp} = V_S$  for  $t \le 400ms$ ;  $V_{OUTP} = V_{OUT}$  for  $t \le 400ms$ ;  $R_{ext} = 12.4K\Omega \pm 1\%$ ).

Symbol	Parameter	Test Condition		Тур.	Max.	Unit
I <sub>ccq</sub>	Vcc Quiescent Current	All Outputs Off		1	3	mA
I <sub>sq</sub>	Vs Quiescent Current	All Outputs Off		14	25	mA
V <sub>ccu</sub>	$V_{cc}$ Undervoltage Threshold	See Note 4	3	4	4.7	V
V <sub>ccr</sub>	$V_{cc}$ Range for RES1 and RES2 Operation		3			V
R <sub>on</sub>	On Resistance	$ \begin{array}{ll} I_{o} = 1A & T_{j} = 125^{\circ}C \\ T_{j} = 25^{\circ}C \end{array} $			750 450	mΩ mΩ
I <sub>o off</sub>	Off State Output Current	$\begin{array}{l} \text{Outputs Off} \\ 1.4 \text{V} \leq \text{V}_{\text{o}} \leq \text{V}_{\text{s}} \\ \text{V}_{\text{outp}} = \text{V}_{\text{sp}} = 40 \text{V} \end{array}$	1 1	2.5	4 10	mA mA
V <sub>outf</sub>	Output Voltage During Flyback	$I_o = 1A$ Output Off T <sub>j</sub> = 25°C T <sub>j</sub> = 125°C			V <sub>s</sub> +1.3 V <sub>s</sub> +1.1	V V
Igndf	Current to GND during Flyback (see note 5)	$I_o = 1A$ Output Off $V_s = 24V$ $V_{sp} = 40V$		17 20	44 52	mA mA
l <sub>outr</sub>	Reverse Leakage Current	$V_{sp} - V_o = 40V$			500	μΑ
VinH	High Input Level of SCLK, SDI, CS, RES1, RES2		0.7*V <sub>cc</sub>		V <sub>cc</sub> +0.3	V
VinL	Low Input Level of SCLK, SDI, CS, RES1, RES2		- 0.3		0.3*Vcc	V
VREShys	Hysteresis of Reset Inputs RES1, RES2		0.3		1	V
linRESH	Input Current on RES1,RES2	$\begin{array}{l} RES_i = H; \ \text{-}2V \leq V_{sp} \leq 8V \\ RES_i = H; \ 8V \leq V_{sp} \leq 40V \end{array}$	- 10 5		10 10	μΑ μΑ
l <sub>in</sub>	Input Current on SCLK,SDI,CS	$-2V \le Vsp \le 40V$	- 10		10	μA
Vsdoh	High Level SDO Output Voltage	$I_{SDO}$ = -1mA -2V $\leq V_{sp} \leq 40V$	0.9*V <sub>cc</sub>		Vcc	V
V <sub>SDOL</sub>	Low Level SDO Output Voltage	$I_{SDO} = 1 \text{mA} - 2 \text{V} \le \text{V}_{sp} \le 40 \text{V}$			0.4	V
I <sub>SDOZ</sub>	SDO Tristate High-Z Leakage Current	$\begin{array}{l} 0 \leq V_{SDO} \leq V_{cc} \\ - 2V \leq V_{sp} \leq 40V \end{array}$	- 10		10	μΑ
PWM <sub>duty</sub>	PWM Duty Cycle		1/16		15/16	
K <sub>f</sub>	Frequency Accuracy Constant	See Note 6	0.93*K <sub>fn</sub>	K <sub>fn</sub>	1.07*K <sub>fn</sub>	
V <sub>flyth</sub>	Flyback Diagnostic Comparator Threshold	$\begin{array}{l} 40 \geq V_{sp} \geq 8V \\ V_{s} \leq 8V \end{array}$	V <sub>s</sub> – 1 1.5		$V_s - 0.4$	V V
V <sub>offth</sub>	Off State Diagnostic Comparator Threshold		1.5		2	V
l <sub>outl</sub>	Output Current Limitation Threshold	see Note 7			2.5	А
t <sub>dpo</sub>	Delay Time PWM Signal to Out.		5		15	μs
Sov	Output Voltage Rise and Fall Slope   du/dt	(from 10 to 90% of V <sub>o</sub> ) Fig. 2			10	V/µs
S <sub>oc</sub>	Output Current Rise and Fall Slope  di/dt	$0.1 \le lo \le 1.5A$ (from 10 to 90% of $l_0$ )	25		125	mA/μs

#### Notes:

**3.** The mean value is  $I_0 = \frac{1}{T} \int_0^T I_0(t) dt$ ;

4. The outputs are switced off for Vcc  $\leq$  Vccu. The logic is not reseted. For a reset, RES1 or RES2 must be used. 5. This current is measured in the GND - terminal when one single output is in flyback and consists of the supply current added to the value of the output current source and the leakage current of the flyback diode. This leakage current is less than 1% of the nominal flyback current. 6. The PWM frequency is defined by an external capacitor. The PWM oscillator frequency is:  $f_{pwm} = \frac{f_{osc}}{32}$  with  $f_{osc} = \frac{K_f}{Cosc} \cdot 1A/V$  and  $k_{in} = 15 \cdot 10^{-6}$ ;

the range is:  $300Hz \le f_{pwm} \le 3000Hz$ . The OSC Pin can be alternatively driven by an external TTL / CMOS signal. 7. For  $I_{out} \ge I_{outl}$  an internal comparator switches the corresponding output off for the current PWM cycle.





Figure 1: Logic Diagram of PWM Generation.





Figure 3: Test Circuit for Schaffner Pulses.



Figure 4: Synchronous Serial Interface Protocol.



f <sub>clock</sub>	Clock Frequency	min. DC	max. 2MHz
t <sub>ch</sub>	Width of Clock Input High Puls	min. 200ns	
t <sub>cl</sub>	Widh of Clock Input Low Puls	min. 200ns	
t <sub>cicl</sub>	Clock Low Before CS Low	min. 200ns	
t <sub>chcl</sub>	Clock High After CS Low	min. 200ns	
t <sub>clch</sub>	Clock Low Before CS High	min. 200ns	
t <sub>chch</sub>	Clock High After CS High	min. 200ns	
t <sub>ciz</sub>	SDO Low-Z CS Low	min. Ons	max. 400ns
t <sub>zch</sub>	SDO High-Z CS High		max. 400ns
t <sub>su</sub>	SDI Input Setup Time	min. 80ns	
t <sub>h</sub>	SDI Input Hold Time	min. 80ns	
t <sub>d</sub>	SDO Output Delay Time (C <sub>L</sub> = 50pF)		max. 100ns
t <sub>oh</sub>	SDO Output Hold Time	min. Ons	



Bit 3 - 0	PWM1	PWM2	PWM3	PWM4	OUTPUT
0000	15/16	15/16	15/16	15/16	OFF
0001	1/16	15/16	1/16	15/16	ON
0010	2/16	14/16	2/16	14/16	ON
0011	3/16	13/16	3/16	13/16	ON
0100	4/16	12/16	4/16	12/16	ON
0101	5/16	11/16	5/16	11/16	ON
0110	6/16	10/16	6/16	10/16	ON
0111	7/16	9/16	7/16	9/16	ON
1000	8/16	8/16	8/16	8/16	ON
1001	9/16	7/16	9/16	7/16	ON
1010	10/16	6/16	10/16	6/16	ON
1011	11/16	5/16	11/16	5/16	ON
1100	12/16	4/16	12/16	4/16	ON
1101	13/16	3/16	13/16	3/16	ON
1110	14/16	2/16	14/16	2/16	ON
1111	15/16	1/16	15/16	1/16	ON

Figure 5: PWM Generation Function Table.

Figure 6: PWM Information From Microcontroller to QLSD.

Bit. Nr.	Name	Contents
0	P10	PWM Duty Cycle for Channel 1 / Bit 0: LSB
1	P11	PWM Duty Cycle for Channel 1 / Bit 1
2	P12	PWM Duty Cycle for Channel 1 / Bit 2
3	P13	PWM Duty Cycle for Channel 1 / Bit 3 : MSB
4	P20	PWM Duty Cycle for Channel 2 / Bit 0 : LSB
5	P21	PWM Duty Cycle for Channel 2 / Bit 1 :
6	P22	PWM Duty Cycle for Channel 2 / Bit 2 :
7	P23	PWM Duty Cycle for Channel 2 / Bit 3 : MSB
8	P30	PWM Duty Cycle for Channel 3 / Bit 0 : LSB
9	P31	PWM Duty Cycle for Channel 3 / Bit 1 :
10	P32	PWM Duty Cycle for Channel 3 / Bit 2 :
11	P33	PWM Duty Cycle for Channel 3 / Bit 3 : MSB
12	P40	PWM Duty Cycle for Channel 4 / Bit 0 : LSB
13	P41	PWM Duty Cycle for Channel 4 / Bit 1:
14	P42	PWM Duty Cycle for Channel 4 / Bit 2 :
15	P43	PWM Duty Cycle for Channel 4 / Bit 3 : MSB



Bit Nr.	Name	Contents
0	F11	COMP1 State at Positive Edge of PWM1 (0: Vout1 > Vflyth; 1: Vout1 < Vflyth)
1	F12	COMP2 State at Negative Edge of PWM1 (1: V <sub>out1</sub> > V <sub>offth</sub> ; 0 : V <sub>out1</sub> < V <sub>ofth</sub> )
2	F21	COMP1 State at Positive Edge of PWM2 (0: V <sub>out2</sub> > V <sub>flyth</sub> ; 1: V <sub>out2</sub> < V <sub>flyth</sub> )
3	F22	COMP2 State at Negative Edge of PWM2 (1: Vout2 > Vofth; 0 : Vout2 < Vofth)
4	F31	COMP1 State at Positive Edge of PWM3 (0: V <sub>out3</sub> > V <sub>flyth</sub> ; 1: V <sub>out3</sub> < V <sub>flyth</sub> )
5	F32	COMP2 State at Negative Edge of PWM3 (1: V <sub>out3</sub> > V <sub>offth</sub> ; 0 : V <sub>out3</sub> < V <sub>ofth</sub> )
6	F41	COMP1 State at Positive Edge of PWM4 (0: Vout4 > Vflyth; 1: Vout4 < Vflyth)
7	F42	COMP2 State at Negative Edge of PWM4 (1: V <sub>out4 &gt; Voffth</sub> ; 0 : V <sub>out4 &lt; Vofth</sub> )
8	RES1	Logic State of RES1 Input (0: RES1 = L ; 1: RES1 = H)
9	RES2	Logic State of RES2 Input (0: RES2 = L ; 1: RES2 = H)
10	TSDF	Thermal Diagnostic Flag (0: Overtemperature; 1:Normal)
11	C1	Current at Negative Edge of PWM1 (0: Iout > Iouti ; 1: Iout < Iouti)
12	C2	Current at Negative Edge of PWM2 (0: Iout > Iouti; 1: Iout < Iouti)
13	C3	Current at Negative Edge of PWM3 (0: I <sub>out</sub> > I <sub>outt</sub> ; 1: I <sub>out</sub> < I <sub>outt</sub> )
14	C4	Current at Negative Edge of PWM4 (0: Iout > Iouti ; 1: Iout < Iouti)
15	1	Framing Information (always 1)

Figure 7: Diagnostic Information from QLSD to Microcontroller.

## Figure 8.



#### Note:

For safty diagnostic take notice of the following conditions:

$$\begin{split} t_{\text{PWMON}} &\geq t_{\text{dPOMAX}} + t_{\text{C}} + t_{\text{V}} \text{ (see Fig. A)} \\ t_{\text{PWMOFF}} &\geq t_{\text{dPOMAX}} + t_{\text{V}} \text{ (see Fig. B)} \end{split}$$



 $t_V = \frac{V_{outfmax}}{S_{OVMIN}}$ 



#### FUNCTIONAL DESCRIPTION

The U511 is a PWM quad low side driver for inductive loads. The duty cycle of the internal generated PWM signal is set by a microcontroller via a serial interface for each output. An output slope limitation for both dv/dt and di /dt is implemented to reduce RFI. The PWM generation is realized avoiding a simultaneous output switching. As a result, di/dt becomes smaller. Integrated flyback diodes clamp the output voltage during the flyback phase of the low side switches.

The driver is protected against short circuit. An undervoltage shutdown circuit switches off all outputs if  $V_{cc}$  is less then  $V_{ccu}$ . Below the shutdown voltage all outputs remain in off state regardless of the input state. After each malfunction which resets the driver, only the serial link interface can reactivate the normal function. In case of overcurrent ( $I_{out} = I_{out1}$ ), an internal comparator switches the output off. The overcurrent information can be read via the serial link for each driver separately at the negative edge of the corresponding PWM signal.

The interface to the microcontroller is realized with a 16 bit synchronous serial peripheral interface (SPI). If CS is switched low, the serial link becomes active and SDO goes to low impedance. At the rising edge of the SCLK signal, one of the 16 bit of data stored in a shift register appear sequencely at SDO. These data contain the 8 error flags, the status of thermal diagnostic flag and the external reset sources RES1, RES2 and the overcurrent flgs c1...c4. The last bit is framing information (see fig. 7). At each falling edge of SCLK, one of the 16 bits of data sent by the microcontroller is transferred via the SDI input to the driver. These data contain the duty-cycle information for the internal PWM generation (4 times 4 bit). On the rising edge of CS the previously stored information is transferred to the circuits. SDO become now high impedance and SDI is inactive. The serial interface of the QLSD is cascadable with the serial link interface of another QLSD, thus obtaining a 32 bit serial link information wich can control eight inductive loads. For a safety data transfer the takeover of data bits is only realized when the number of SCLK - clocks is n x 16 (n  $\geq$  1).

The PWM duty cycle is set by 4 bit for each output independently via the serial link. If all four bits for an output are zero, the output is turned off, but the error diagnosis will work correctly (see fig. 5 and 6). The PWM frequency is defined by an external capacitor on the OSC pin. Rext defines through the reference current the output current slope, the diagnostic current sink and the internal oscillator frequency (together with  $C_{osc}$ ).

For error diagnosis the voltage on the output is measured during the on and off state of the particular output driver. Upon the rising edge of the PWM signal (at this moment the power output is off and will be switched on) the status of COMP1 is stored into an internal latch. On the falling edge of the PWM signal ( the power output is on and will be switched off) the status of COMP2 is stored into another internal latch. This information can be read via the serial link for each output driver separately (see fig. 7).

The thermal diagnostic switch the thermal flag to 0 in case of overtemperature  $T \geq T_{sd}$ . It will be switched to 1 with the hysteresis  $T_{sdth}$  in case of  $T < T_{sd}$  -  $T_{sdh}$ .

To avoid male functions due to extensive noise or spikes at the supply pins  $V_{CC}$ ,  $V_S$  and  $R_{ext}$  must be blocked externally via capacitors.



ЫМ	mm			inch		
Diwi.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
А			5			0.197
В			2.65			0.104
С			1.6			0.063
D		1			0.039	
E	0.49		0.55	0.019		0.022
F	0.66		0.75	0.026		0.030
G	1.02	1.27	1.52	0.040	0.050	0.060
G1	17.53	17.78	18.03	0.690	0.700	0.710
H1	19.6			0.772		
H2			20.2			0.795
L	21.9	22.2	22.5	0.862	0.874	0.886
L1	21.7	22.1	22.5	0.854	0.870	0.886
L2	17.65		18.1	0.695		0.713
L3	17.25	17.5	17.75	0.679	0.689	0.699
L4	10.3	10.7	10.9	0.406	0.421	0.429
L7	2.65		2.9	0.104		0.114
М	4.25	4.55	4.85	0.167	0.179	0.191
M1	4.63	5.08	5.53	0.182	0.200	0.218
S	1.9		2.6	0.075		0.102
S1	1.9		2.6	0.075		0.102
Dia1	3.65		3.85	0.144		0.152





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